

F Yu Soldatenkov

List of Publications by Year in descending order

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35
papers

238
citations

1163117

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1058476

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all docs

35
docs citations

35
times ranked

172
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Porous silicon and its applications in biology and medicine. Technical Physics, 2014, 59, 66-77. | 0.7 | 55 |
| 2 | Unstrained epitaxial $\text{In}_x\text{Ga}_{1-x}\text{As}$ films obtained on porous GaAs. Technical Physics Letters, 1999, 25, 852-854. | 0.7 | 19 |
| 3 | Anodic processes in the chemical and electrochemical etching of Si crystals in acid-fluoride solutions: Pore formation mechanism. Semiconductors, 2017, 51, 458-472. | 0.5 | 17 |
| 4 | Fast pulsed gallium arsenide heterostructure diodes. Semiconductors, 2009, 43, 1055-1057. | 0.5 | 12 |
| 5 | Surface of porous silicon under hydrophilization and hydrolytic degradation. Semiconductors, 2014, 48, 1211-1216. | 0.5 | 12 |
| 6 | GaSb-based photovoltaic laser-power converter for the wavelength $\lambda \approx 1550$ nm. Semiconductors, 2015, 49, 1079-1082. | 0.5 | 12 |
| 7 | A decrease in ohmic losses and an increase in power in GaSb photovoltaic converters. Semiconductors, 2011, 45, 1219-1226. | 0.5 | 11 |
| 8 | Control over carrier lifetime in high-voltage p-i-n diodes based on $\text{In}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ heterostructures. Semiconductors, 2007, 41, 211-214. | 0.5 | 10 |
| 9 | Study of deep levels in GaAs $\text{p}^+\text{i}^-\text{n}$ structures. Semiconductors, 2016, 50, 924-928. | 0.5 | 9 |
| 10 | Deep-level centers in undoped p-GaAs layers grown by liquid phase epitaxy. Semiconductors, 2000, 34, 541-544. | 0.5 | 7 |
| 11 | Defect engineering for carrier lifetime control in high voltage GaAs power diodes. , 2014, , . | | 7 |
| 12 | Misfit dislocation-related deep levels in $\text{InGaAs}/\text{GaAs}$ and $\text{GaAsSb}/\text{GaAs}$ $\text{p}^+\text{i}^-\text{n}$ heterostructures and the effect of these on the relaxation time of nonequilibrium carriers. Journal of Applied Physics, 2018, 123, 161588. | 2.5 | 7 |
| 13 | Estimation of quality of GaAs substrates used for constructing semiconductor power devices. Technical Physics, 2014, 59, 1566-1569. | 0.7 | 6 |
| 14 | Effect of Dislocation-related Deep Levels in Heteroepitaxial $\text{InGaAs}/\text{GaAs}$ and $\text{GaAsSb}/\text{GaAs}$ $\text{p}^+\text{i}^-\text{n}$ Structures on the Relaxation time of Nonequilibrium Carriers. Semiconductors, 2018, 52, 165-171. | 0.5 | 6 |
| 15 | Dissimilar gold nanoclusters at $\text{GaAs}(0001)$ surface: Formation chemistry, structure, and localized plasmons. Applied Surface Science, 2020, 507, 144982. | 6.1 | 6 |
| 16 | Current flow mechanism in ohmic contact to n-4H-SiC. Semiconductors, 2010, 44, 463-466. | 0.5 | 5 |
| 17 | $\text{GaAs}/\text{AlGaAs}$ heterostructure thyristors with completely optical transfer of emitter current. Semiconductors, 2011, 45, 515-518. | 0.5 | 4 |
| 18 | Deep-level defects in high-voltage AlGaAs $\text{p}^+\text{i}^-\text{n}$ diodes and the effect of these defects on the temperature dependence of the minority carrier lifetime. Journal of Applied Physics, 2020, 128, 095705. | 2.5 | 4 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Annealing atmosphere influence on contact resistivity of ohmic Pd/Ge/Au contact to n-GaAs. <i>Nanosystems: Physics, Chemistry, Mathematics</i> , 2018, 9, 789-792. | 0.4 | 4 |
| 20 | Porous-Semiconductor-Based Hydrogen-Permeable Membrane. <i>Industrial & Engineering Chemistry Research</i> , 2007, 46, 2263-2267. | 3.7 | 3 |
| 21 | Temperature stability of contact systems for GaSb-based photovoltaic converters. <i>Semiconductors</i> , 2014, 48, 1248-1253. | 0.5 | 3 |
| 22 | A Study of Ohmic Contacts of Power Photovoltaic Converters. <i>Technical Physics Letters</i> , 2018, 44, 1198-1200. | 0.7 | 3 |
| 23 | Gold Nanoclusters at the Interface Au/GaAs(001): Preparation, Characterization, and Plasmonic Spectroscopy. <i>Semiconductors</i> , 2018, 52, 1849-1852. | 0.5 | 3 |
| 24 | Optical Spectroscopy of Schottky Nanostructures Au/GaAs: Plasmon Resonances and Anisotropy. <i>Semiconductors</i> , 2020, 54, 1877-1880. | 0.5 | 3 |
| 25 | Polarization Spectroscopy of Anisotropic Plasmons in Self-Oriented Nanoclusters of Gold on Monolayer of Nitrogen Atoms Chemisorbed at GaAs(001) Surface. <i>Physica Status Solidi (B): Basic Research</i> , 2022, 259, 2100394. | 1.5 | 3 |
| 26 | Au- and Ag-Containing Contacts to GaSb-Photovoltaic Converters. <i>IEEE Electron Device Letters</i> , 2022, 43, 418-421. | 3.9 | 2 |
| 27 | Fast photonic switches based on GaAs nanostructures. <i>Technical Physics Letters</i> , 2006, 32, 372-376. | 0.7 | 1 |
| 28 | Effect of a wideband heteroepitaxial emitter on dynamics of turn-off switching of high-voltage power GaAs p-i-n diodes. <i>Journal of Physics: Conference Series</i> , 2016, 690, 012038. | 0.4 | 1 |
| 29 | Capacitance Spectroscopy of Heteroepitaxial AlGaAs/GaAs δ -Layer Structures. <i>Semiconductors</i> , 2020, 54, 1260-1266. | 0.5 | 1 |
| 30 | Deep level defects in GaAs gradual p-i-n junctions after neutron irradiation. <i>Journal of Physics: Conference Series</i> , 2022, 2227, 012019. | 0.4 | 1 |
| 31 | Effect of Neutron Irradiation on the Spectrum of Deep-Level Defects in GaAs Grown by Liquid-Phase Epitaxy in a Hydrogen and Argon Atmosphere. <i>Semiconductors</i> , 0, , . | 0.5 | 1 |
| 32 | GaAs-Ge non-planar composite epitaxial heterostructures: LPE growth and cathodoluminescence investigations. , 0, , . | | 0 |
| 33 | GaAs- Al _{0.3} B _{0.5} heterostructures for high-speed power diodes manufacturing. <i>Journal of Physics: Conference Series</i> , 2015, 661, 012066. | 0.4 | 0 |
| 34 | Effect of nitride chemical passivation of the surface of GaAs photodiodes on their characteristics. <i>Journal of Physics: Conference Series</i> , 2016, 769, 012068. | 0.4 | 0 |
| 35 | Gold nanoclusters on GaAs(001) surface: atomic force microscopy and optical spectroscopy of plasmons. <i>Journal of Physics: Conference Series</i> , 2019, 1400, 055005. | 0.4 | 0 |